

N-Channel 75-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ)
75	0.037 at $V_{GS} = 10$ V	16^e	8 nC
	0.046 at $V_{GS} = 4.5$ V	16^e	

FEATURES

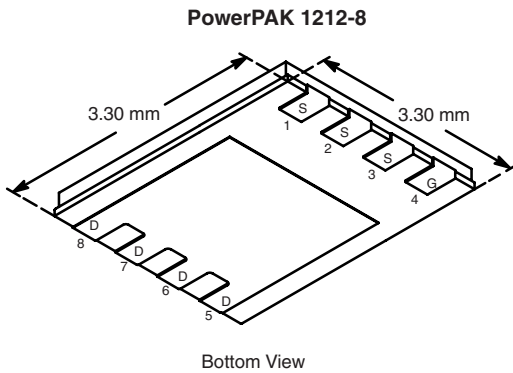
- TrenchFET[®] Power MOSFET
- Low Thermal Resistance PowerPAK[®] Package with Small Size and Low 1.07 mm Profile



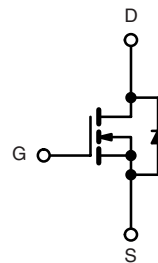
RoHS
COMPLIANT

APPLICATIONS

- Primary Side Switch



Ordering Information: Si7812DN-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	75	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	16^e	A
	$T_C = 70$ °C	16^e	
	$T_A = 25$ °C	$7.2^{a, b}$	
	$T_A = 70$ °C	$5.7^{a, b}$	
Pulsed Drain Current	I_{DM}	25	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	16^e	
	$T_A = 25$ °C	$3.2^{a, b}$	
Avalanche Current	I_{AS}	15	
Single-Pulse Avalanche Energy	E_{AS}	11	mJ
Maximum Power Dissipation	$T_C = 25$ °C	52	W
	$T_C = 70$ °C	33	
	$T_A = 25$ °C	$3.8^{a, b}$	
	$T_A = 70$ °C	$2.4^{a, b}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{c, d}		260	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. $t = 10$ sec.

c. See Solder Profile (<http://www.vishay.com/ppg?73257>). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

e. Package limited.

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	$t \leq 10$ sec	R_{thJA}	26	33	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.9	2.4	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Maximum under Steady State conditions is 81 °C/W.

SPECIFICATIONS $T_J = 25$ °C, unless otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$ V, $I_D = 250$ μ A	75			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250$ μ A		65		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 6.4		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250$ μ A	1.0	2.0	3.0	V
		$V_{DS} = V_{GS}$, $I_D = 5$ mA		2.3		
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 20$ V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 75$ V, $V_{GS} = 0$ V			1	μ A
		$V_{DS} = 75$ V, $V_{GS} = 0$ V, $T_J = 55$ °C			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5$ V, $V_{GS} = 10$ V	25			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 7.2$ A		0.031	0.037	Ω
		$V_{GS} = 4.5$ V, $I_D = 6.4$ A		0.038	0.046	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15$ V, $I_D = 7.2$ A		23		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 35$ V, $V_{GS} = 0$ V, $f = 1$ MHz		840		pF
Output Capacitance	C_{oss}			110		
Reverse Transfer Capacitance	C_{riss}			50		
Total Gate Charge	Q_g	$V_{DS} = 38$ V, $V_{GS} = 10$ V, $I_D = 7.2$ A		16	24	nC
				8	12	
Gate-Source Charge	Q_{gs}	$V_{DS} = 38$ V, $V_{GS} = 4.5$ V, $I_D = 7.2$ A		2.8		
Gate-Drain Charge	Q_{gd}			3.6		
Gate Resistance	R_g	$f = 1$ MHz		1		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 38$ V, $R_L = 6.7$ Ω $I_D \cong 5.7$ A, $V_{GEN} = 4.5$ V, $R_g = 1$ Ω		20	30	ns
Rise Time	t_r			130	200	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	t_f			50	75	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 38$ V, $R_L = 6.7$ Ω $I_D \cong 5.7$ A, $V_{GEN} = 10$ V, $R_g = 1$ Ω		15	25	
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			35	40	
Fall Time	t_f			10	15	



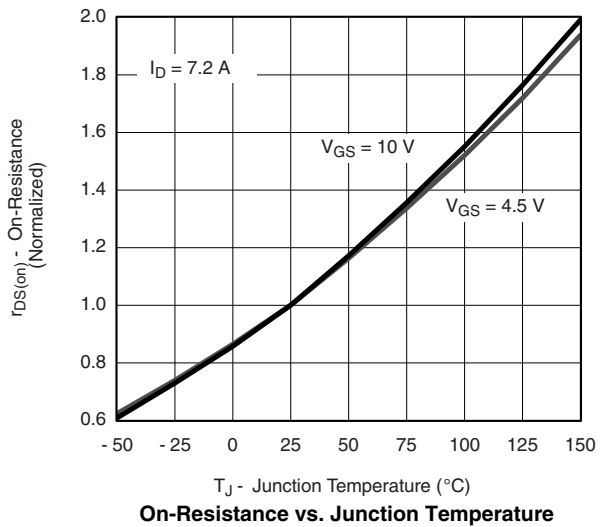
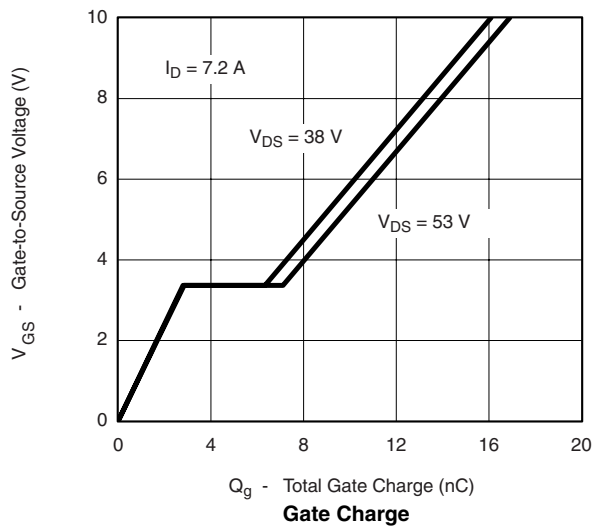
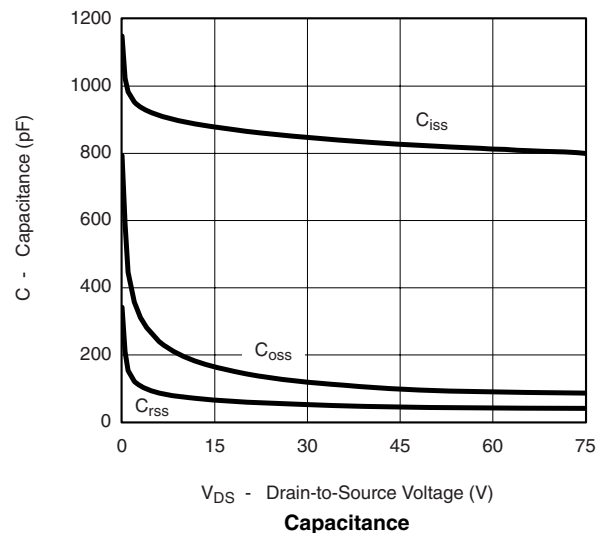
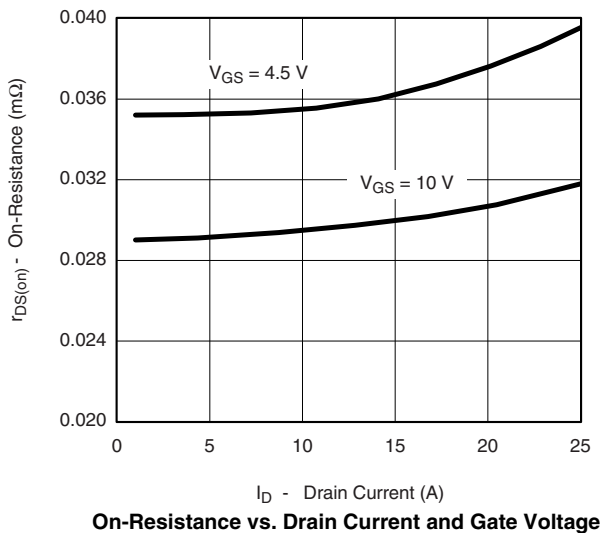
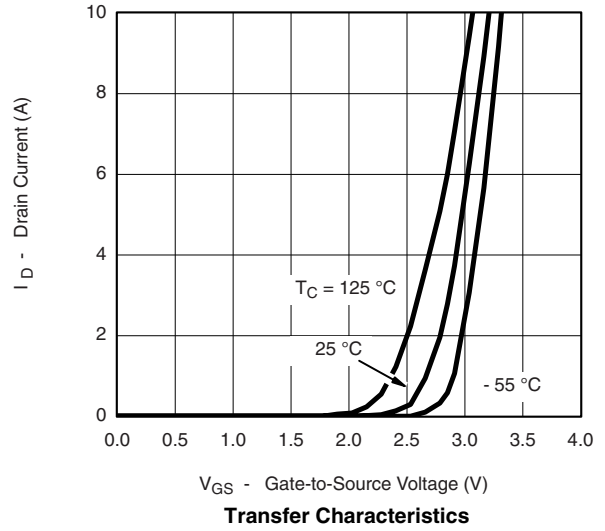
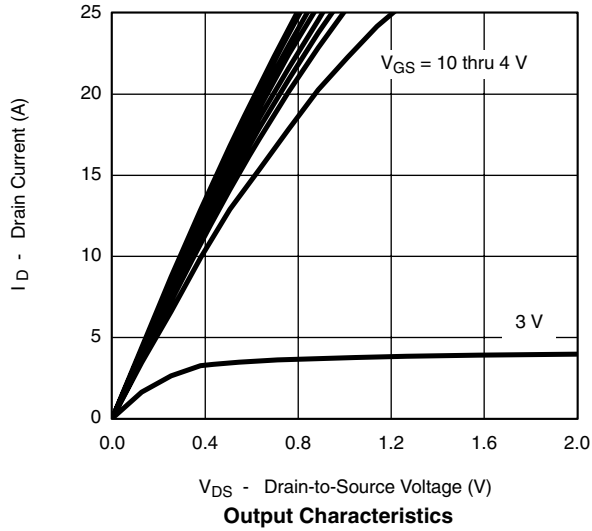
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			16	A
Pulse Diode Forward Current ^a	I_{SM}				25	
Body Diode Voltage	V_{SD}	$I_S = 3.2\text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 5.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^\circ\text{C}$		30	50	ns
Body Diode Reverse Recovery Charge	Q_{rr}			40	65	nC
Reverse Recovery Fall Time	t_a			23		ns
Reverse Recovery Rise Time	t_b			7		

Notes:

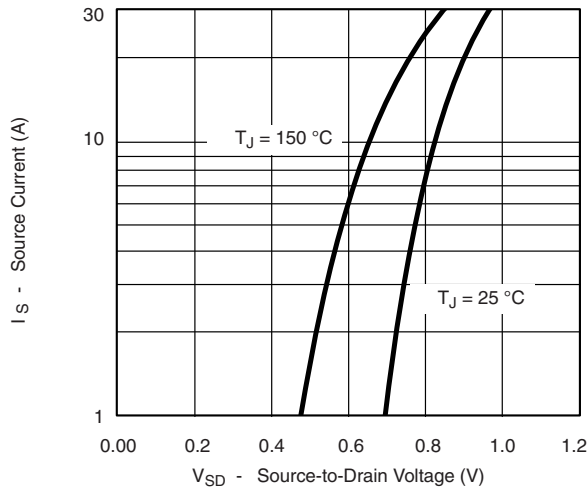
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

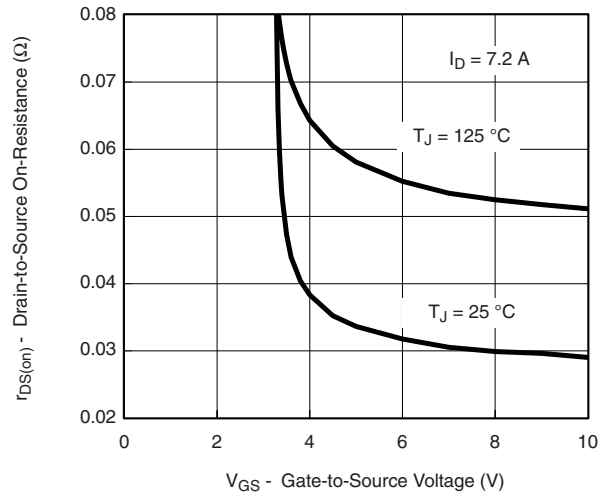
TYPICAL CHARACTERISTICS 25 °C unless noted



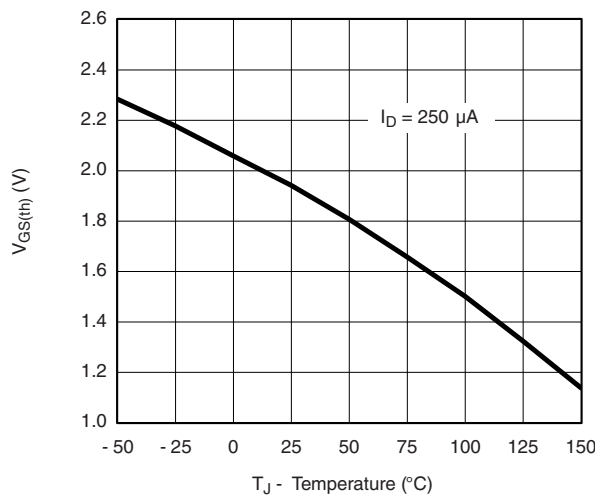
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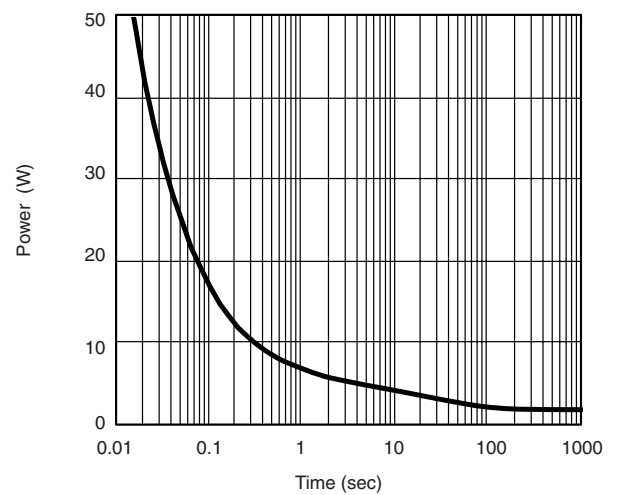
Source-Drain Diode Forward Voltage



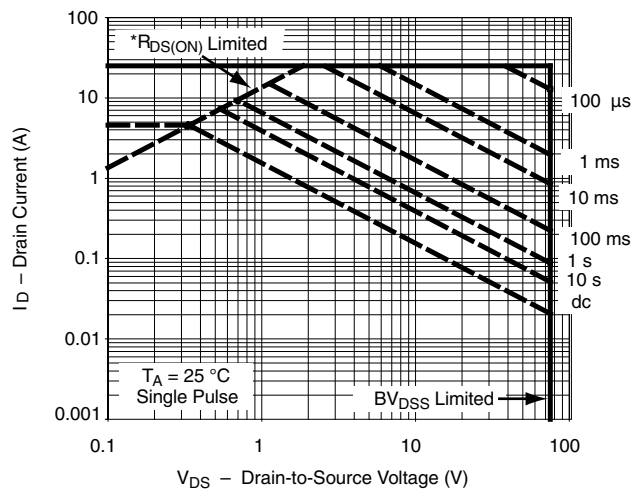
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



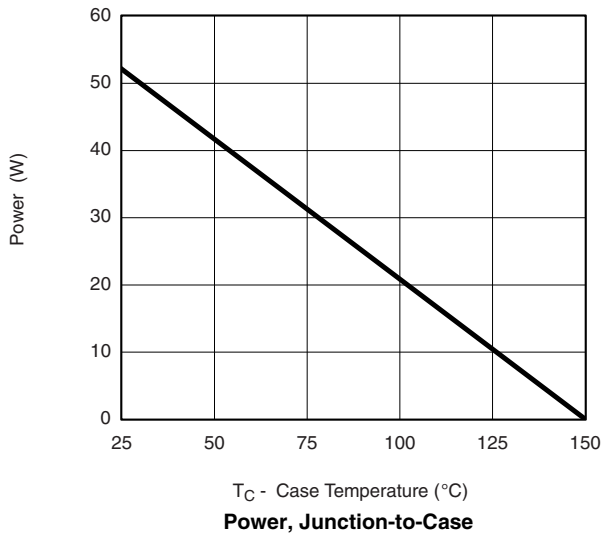
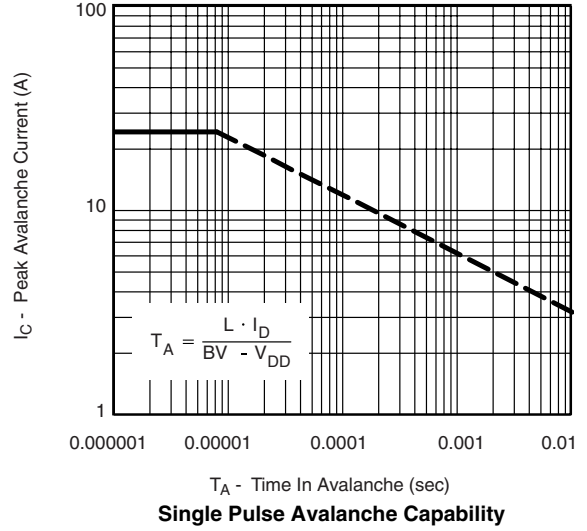
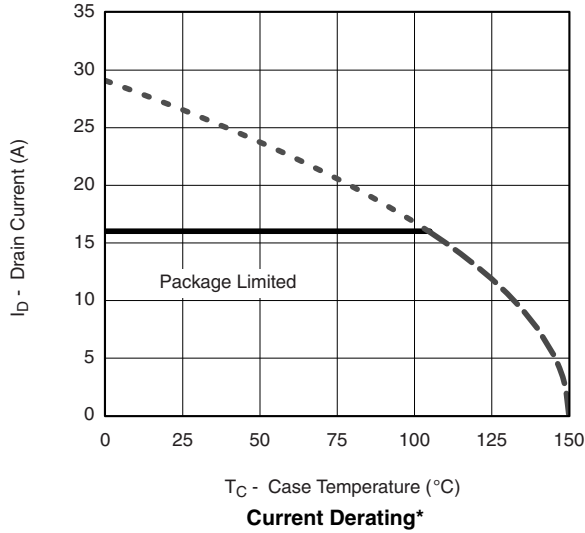
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $r_{DS(on)}$ is specified

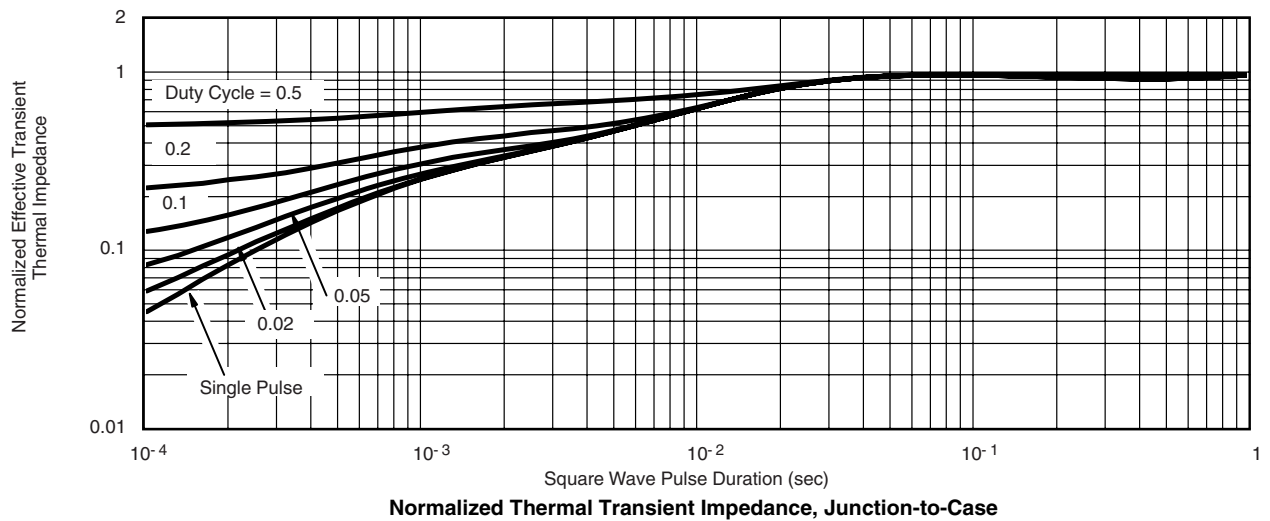
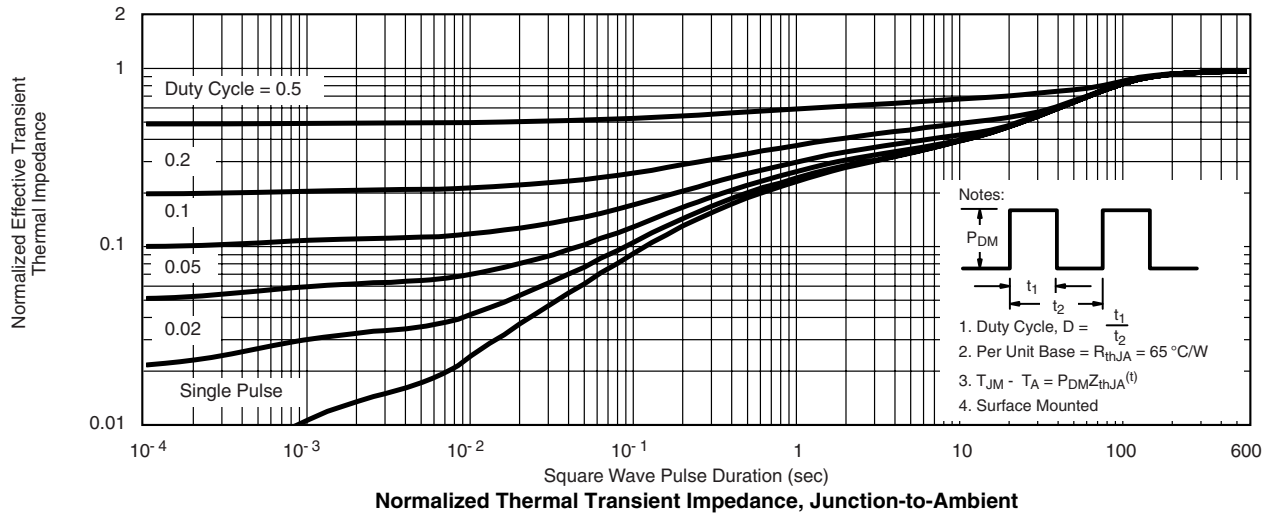
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C unless noted



*The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C unless noted



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